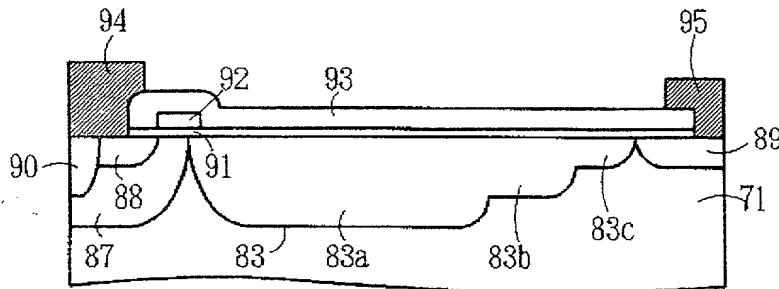


Fig. 1



- |      |                          |     |                                     |
|------|--------------------------|-----|-------------------------------------|
| 71:  | n-type silicon substrate | 89: | n-type drain region                 |
| 83:  | p-type offset region     | 90: | p <sup>+</sup> -type contact region |
| 83a: | First p-type sub-region  | 91: | Gate insulation film                |
| 83b: | Second p-type sub-region | 92: | Gate electrode                      |
| 83c: | Third p-type sub-region  | 93: | Insulation film                     |
| 87:  | p-type base region       | 94: | Source electrode                    |
| 88:  | n-type source region     | 95: | Drain electrode                     |

Fig. 2

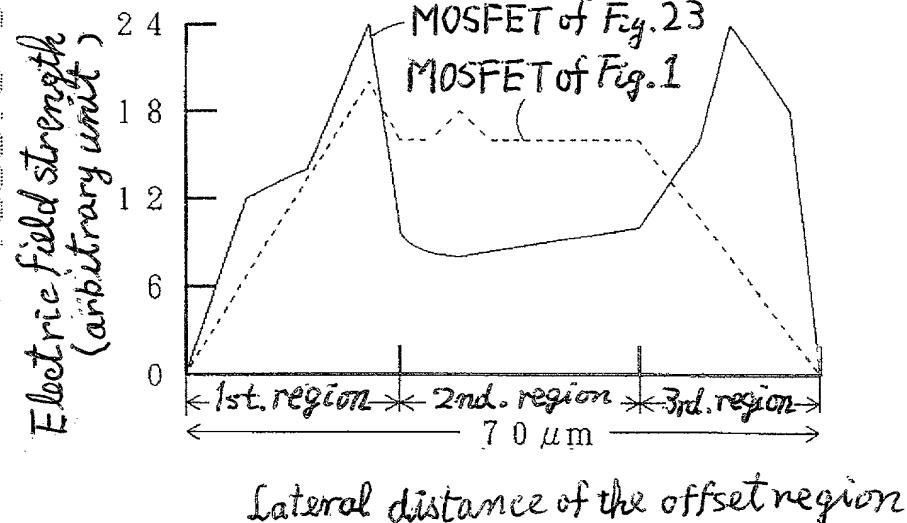


Fig. 3

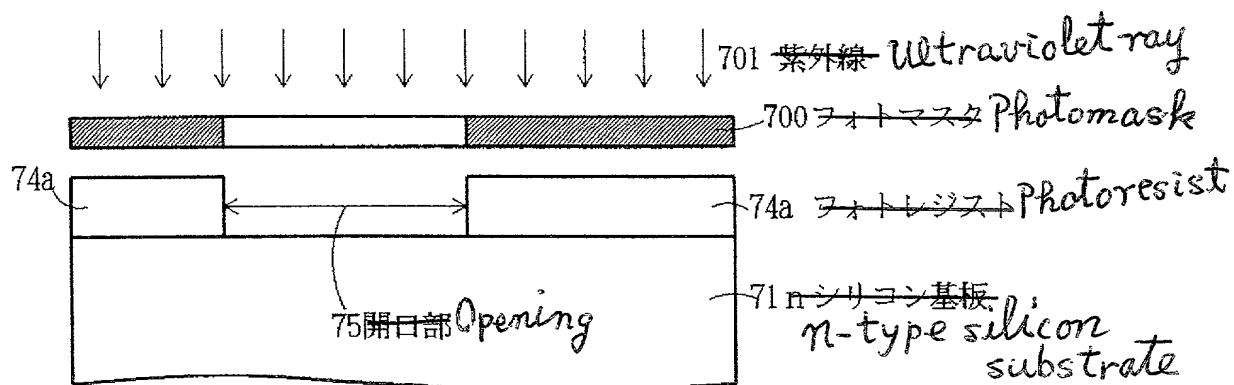


Fig. 4

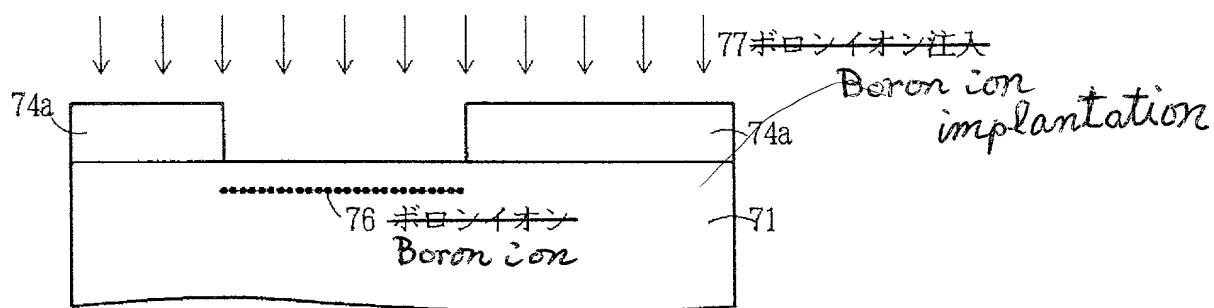


Fig. 5

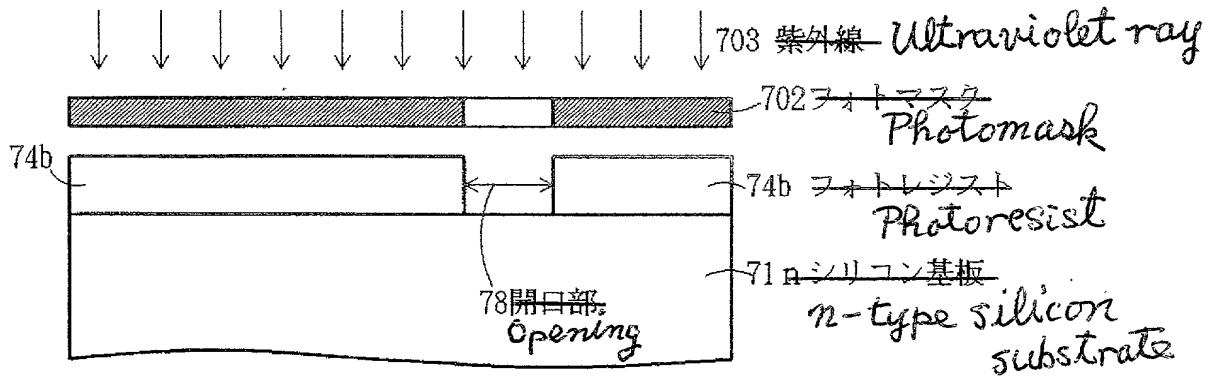


Fig. 6

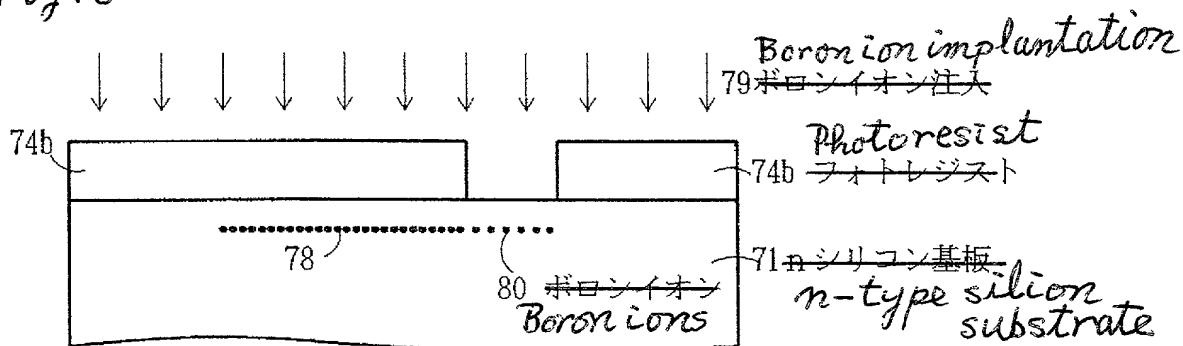


Fig. 7

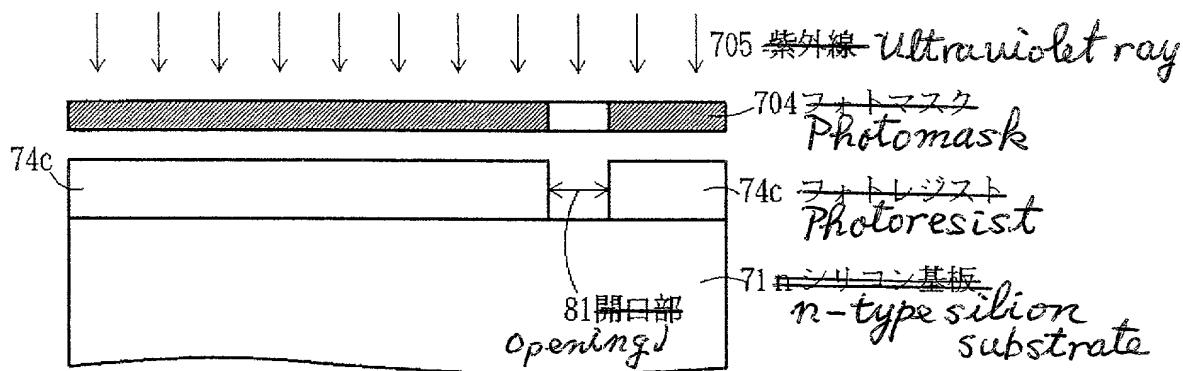


Fig. 8

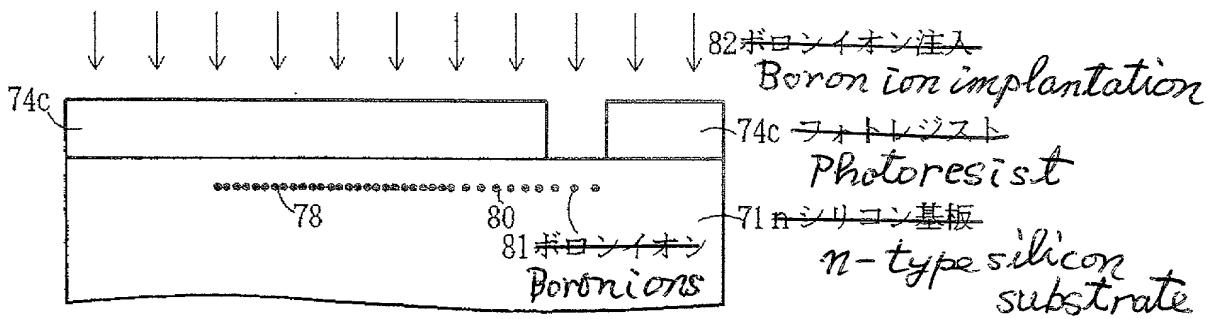


Fig. 9

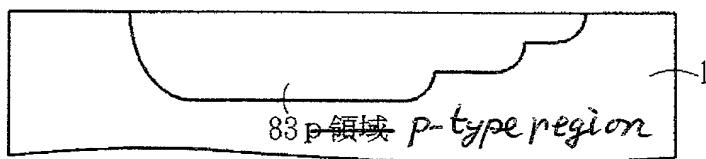


Fig. 10

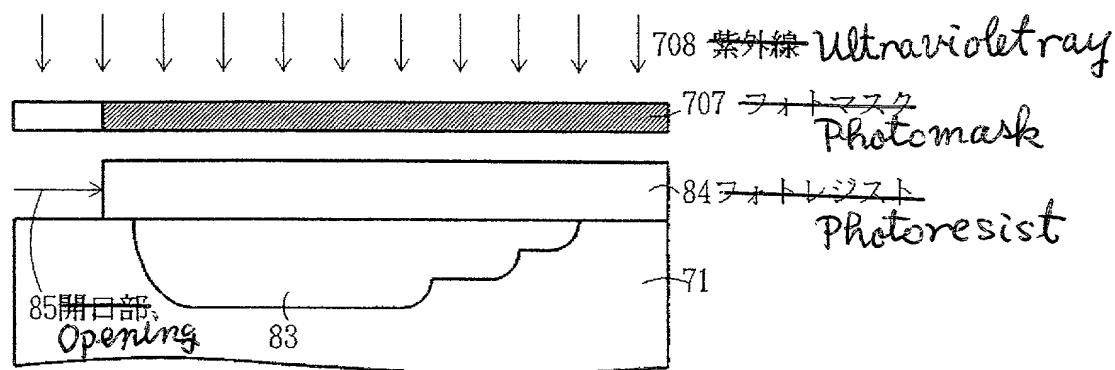


Fig. 11

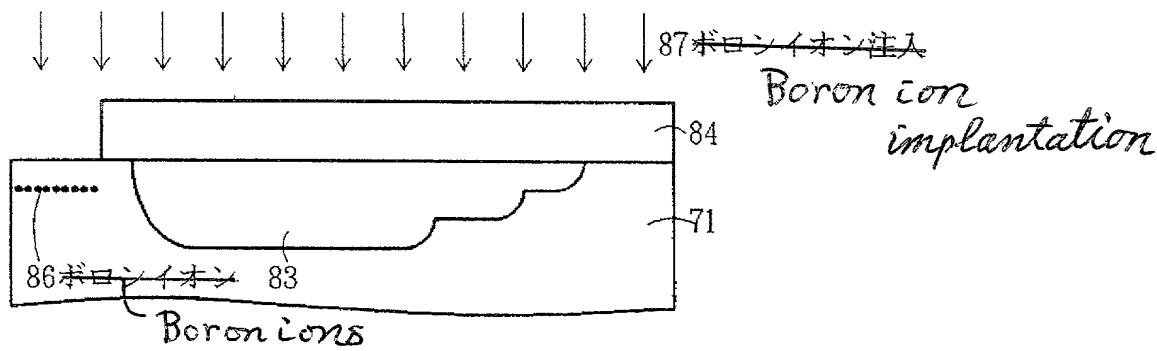


Fig. 12

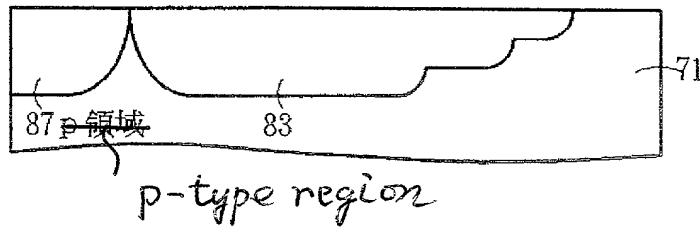
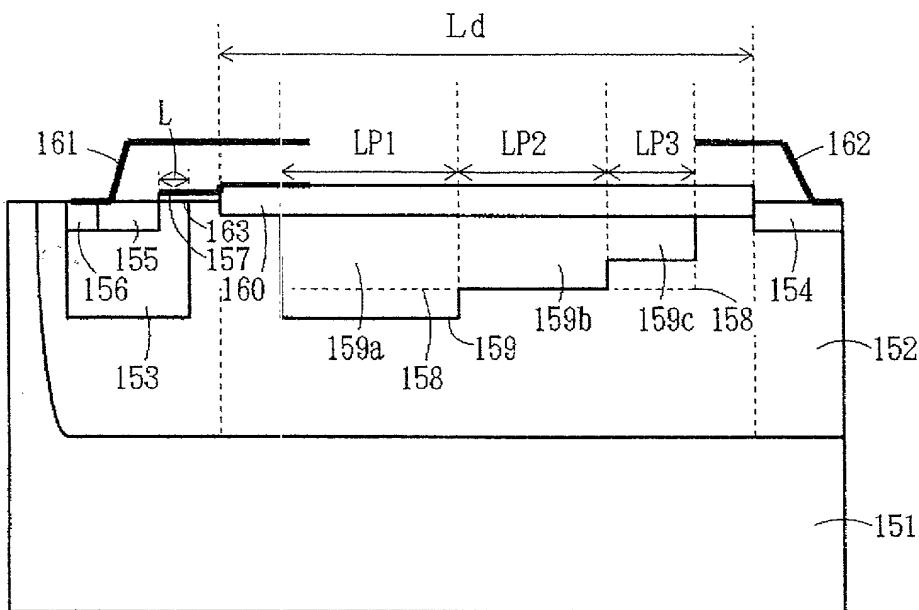


Fig. 13



- 151: p-type substrate
- 152: n-type well region
- 153: p-type base region
- 154: n-type drain region
- 155: n-type source region
- 156: p<sup>+</sup>-type contact region
- 157: Gate electrode
- 158: Boron diffusion depth
- 159: p-type diffusion region (p-type offset region)
- 159a: First p-type sub-region
- 159b: Second p-type sub-region
- 159c: Third p-type sub-region
- 160: Insulation film
- 161: Source electrode
- 162: Drain electrode
- 163: Gate insulation film

Fig. 14

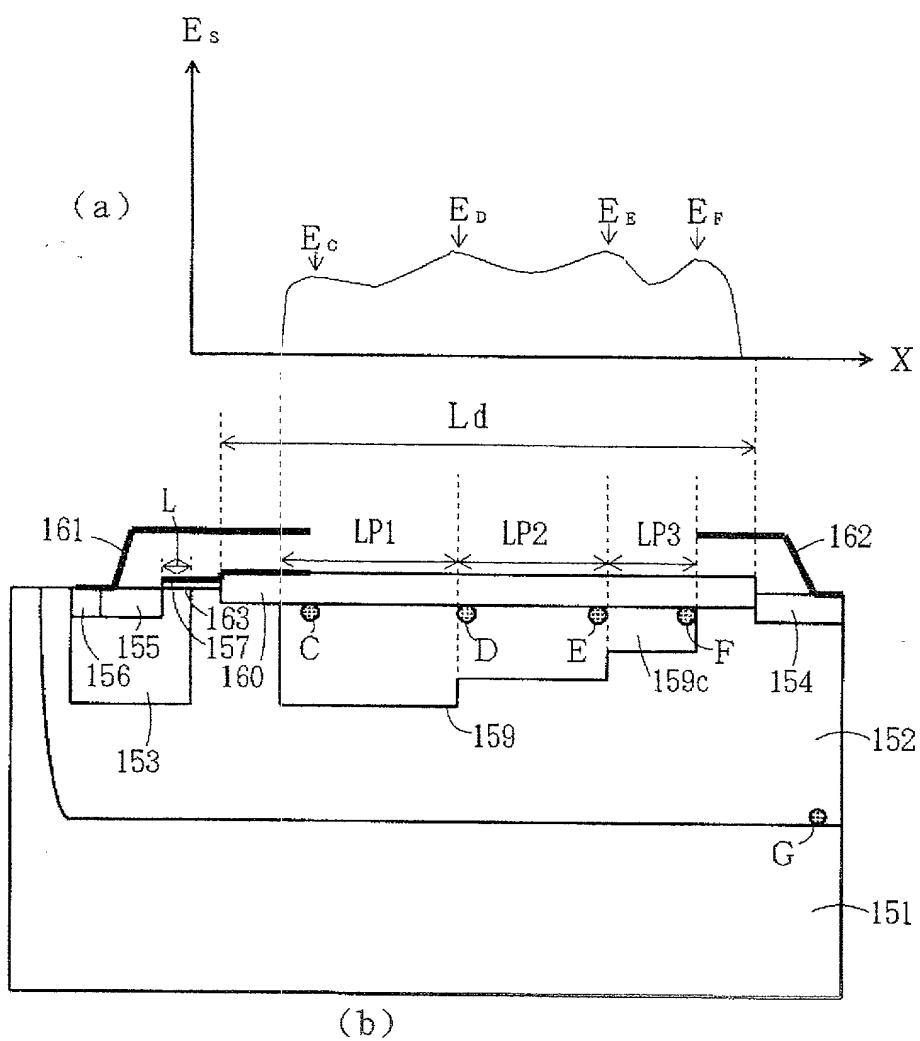
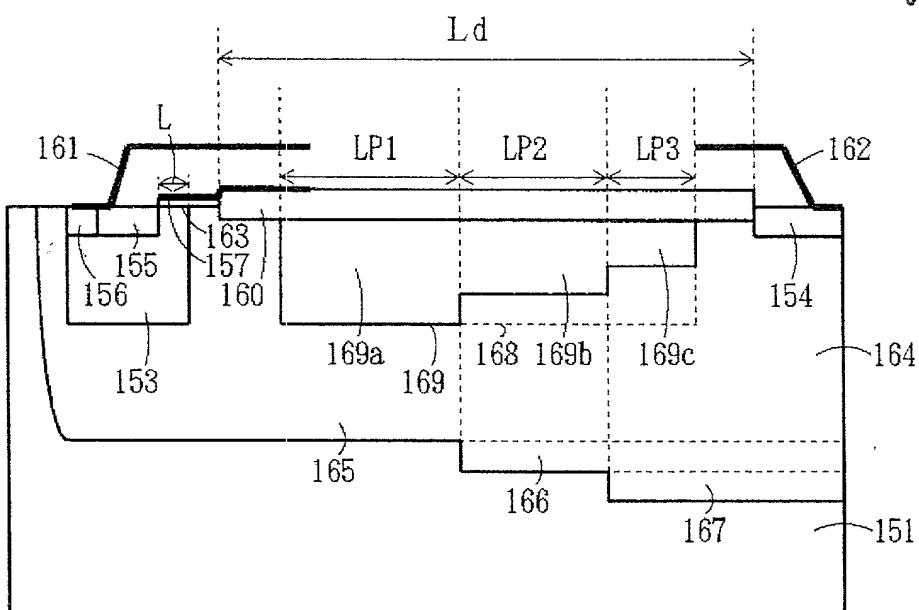


Fig. 15



- 164: n-type well region
- 165: First well sub-region
- 166: Second well sub-region
- 167: Third well sub-region
- 168: Boron diffusion depth
- 169: p-type diffusion region
- 169a: First p-type sub-region
- 169b: Second p-type sub-region
- 169c: Third p-type sub-region

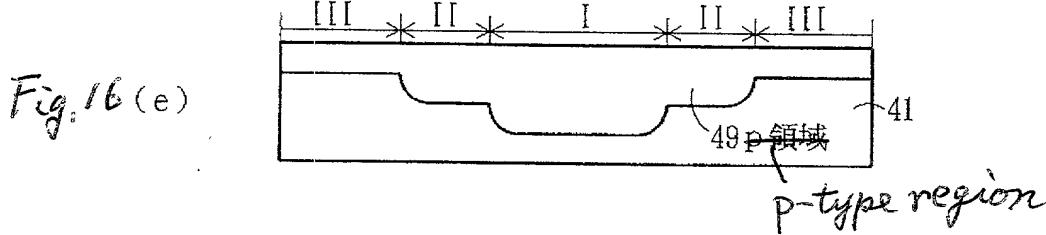
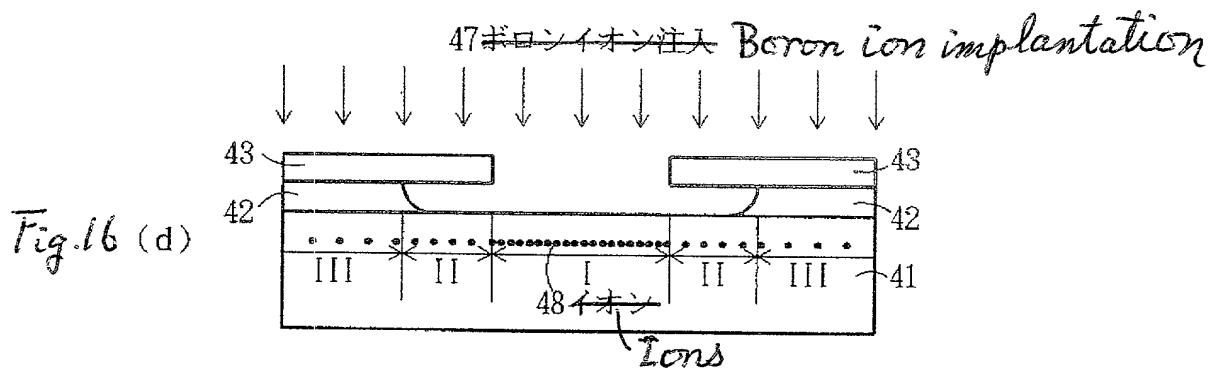
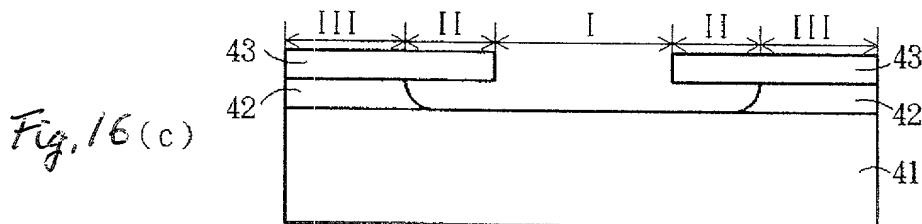
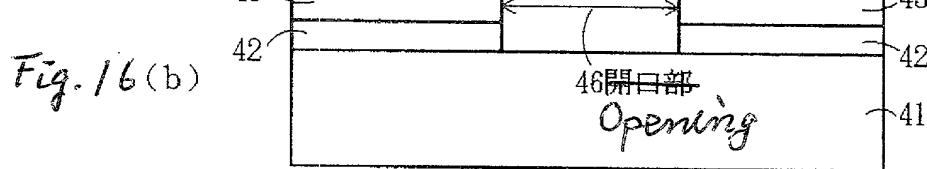
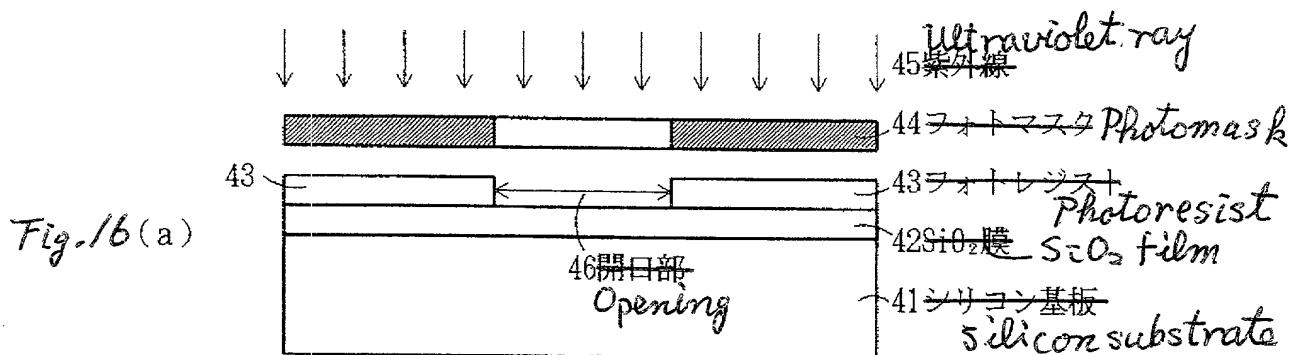


Fig.17 (a)

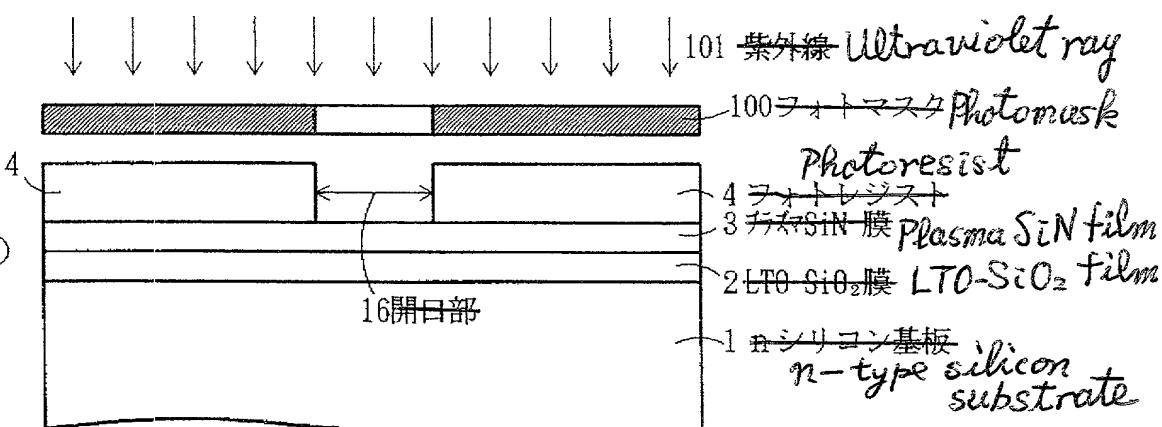


Fig.17 (b)

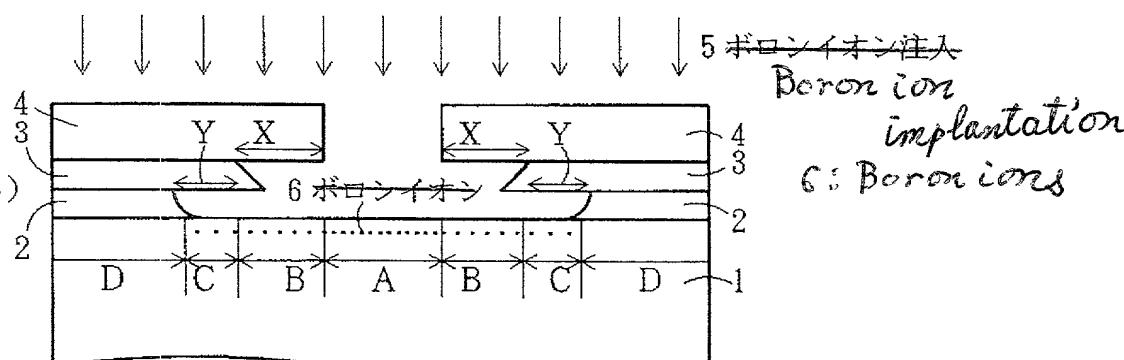


Fig.17 (c)



Fig.17 (d)

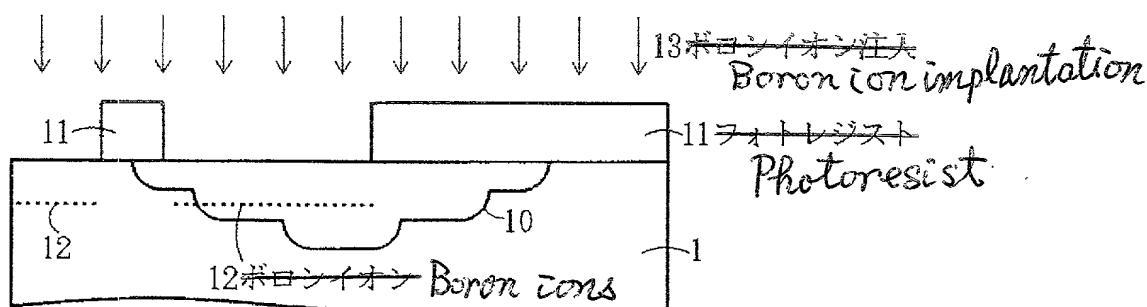


Fig.17 (e)

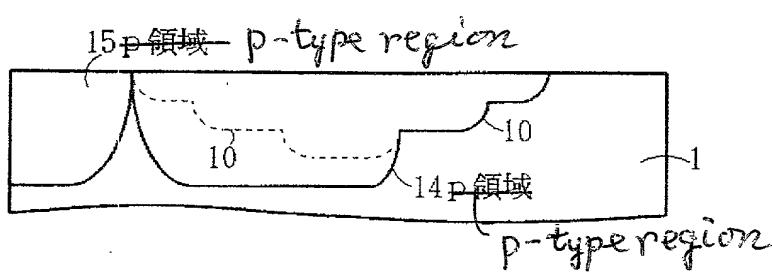


Fig. 18(a)

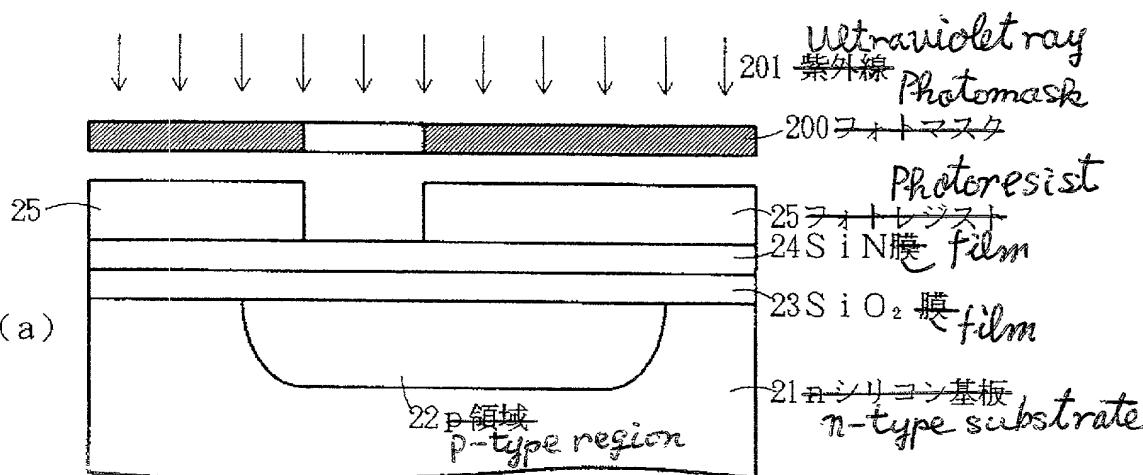


Fig. 18(b)

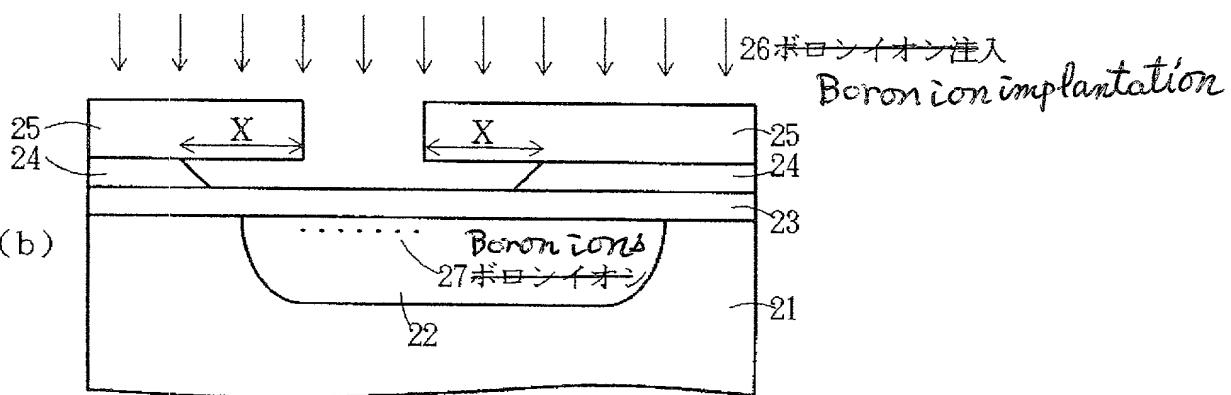


Fig. 18(c)

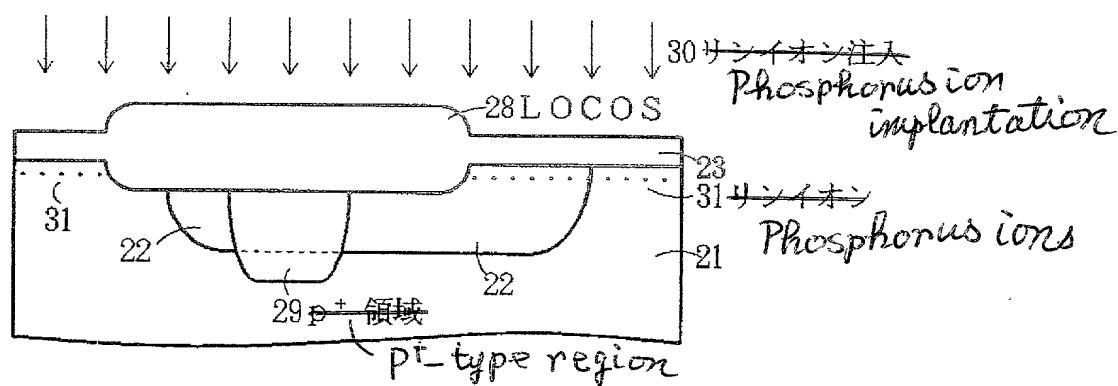


Fig. 18(d)

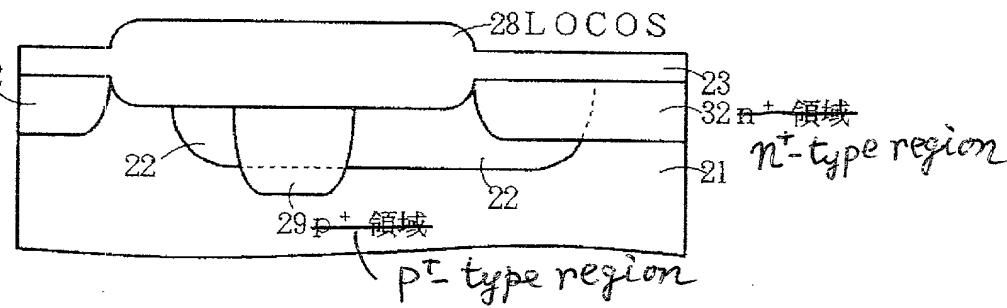


Fig. 19

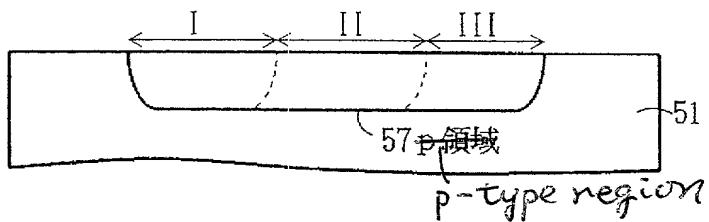


Fig. 20

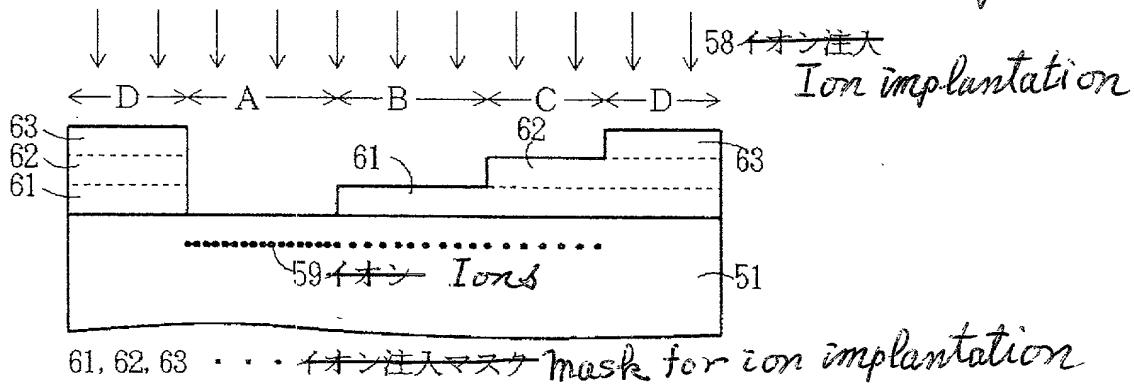
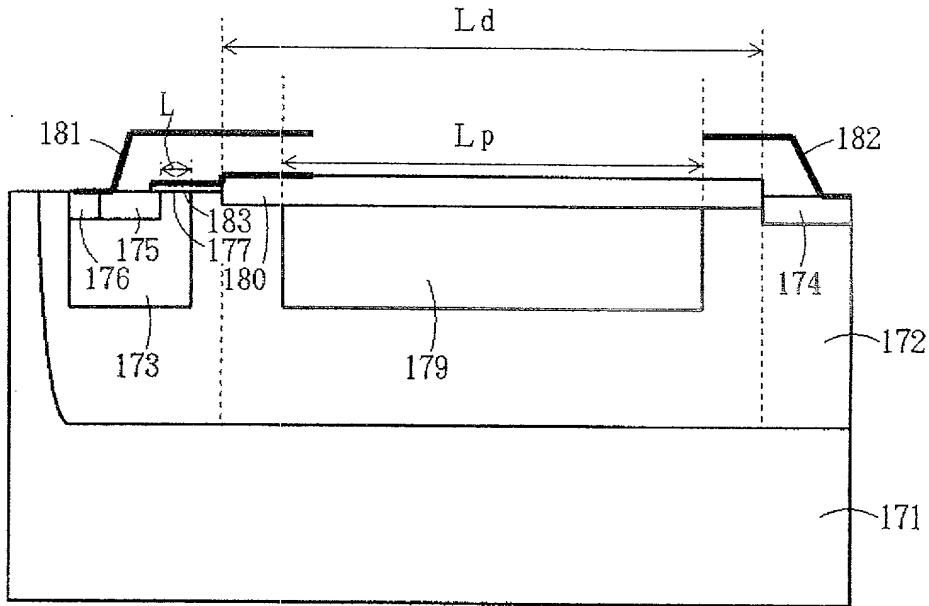


Fig. 21



171: p-type substrate

177: Gate electrode

172: n-type well region

179: p-type diffusion region (p-type offset region)

173: p-type base region

180: Insulation film

174: n-type drain region

181: Source electrode

175: n-type source region

182: Drain electrode

176: p<sup>+</sup>-type contact region

183: Gate oxide film

Fig. 22(a)

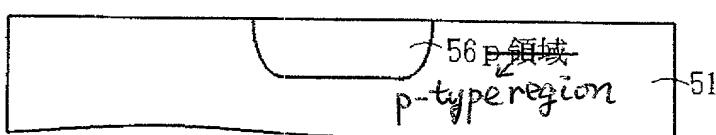
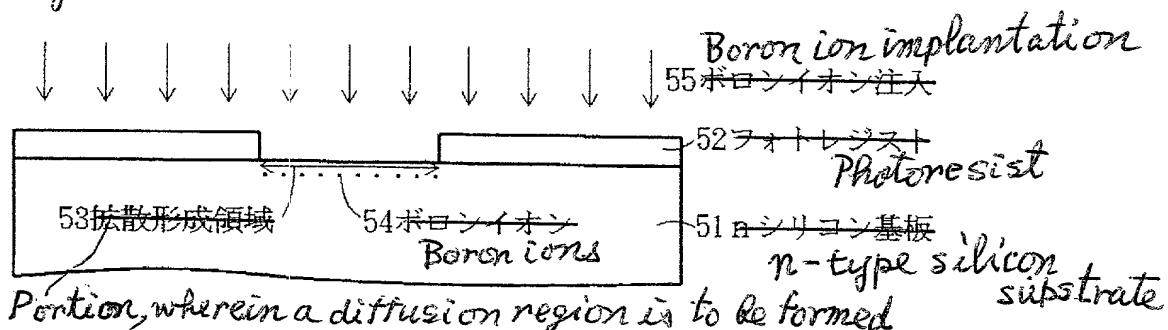


Fig. 22(b)

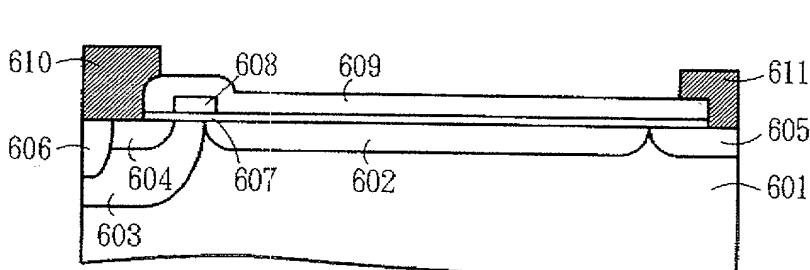


Fig. 23

- |  |                       |
|--|-----------------------|
| 601: <i>n</i> -type silicon substrate                      | 607: Gate oxide film  |
| 602: <i>p</i> -type region ( <i>p</i> -type offset region) | 608: Gate electrode   |
| 603: <i>p</i> -type region ( <i>p</i> -type base region)   | 609: Insulation film  |
| 604: <i>n</i> -type source region                          | 610: Source electrode |
| 605: <i>n</i> -type drain region                           | 611: Drain electrode  |
| 606: <i>p</i> -type contact region                         |                       |

Fig. 24

